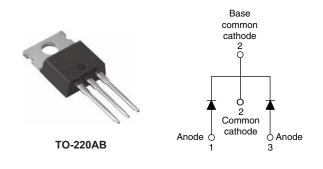
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VS-MUR1020CTPbF, VS-MUR1020CT-N3

Vishay Semiconductors

Ultrafast Rectifier, 10 A FRED Pt[®]



PRODUCT SUMMARY						
Package	TO-220AB					
I _{F(AV)}	2 x 5 A					
V _R	200 V					
V _F at I _F	0.87 V					
t _{rr} typ.	See Recovery table					
T _J max.	175 °C					
Diode variation	Common cathode					

FEATURES

- Ultrafast recovery time
- · Low forward voltage drop
- 175 °C operating junction temperature
- Low leakage current
- Designed and qualified according to JEDĔC[®]-JESD 47
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

DESCRIPTION / APPLICATIONS

VS-MUR.. series are the state of the art ultrafast recovery rectifiers specifically designed with optimized performance of forward voltage drop and ultrafast recovery time.

The planar structure and the platinum doped life time control, guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, UPS, DC/DC converters as well as freewheeling diode in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS								
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS				
Peak repetitive reverse voltage	V _{RRM}		200	V				
Average rectified forward currentper leg	le		5					
total device	IF(AV)	Rated V _R , T _C = 149 °C	10					
Non-repetitive peak surge current per leg	I _{FSM}		50	А				
Peak repetitive forward current per leg	I _{FM}	Rated V _R , square wave, 20 kHz T _C = 149 °C	10					
Operating junction and storage temperatures	T _J , T _{Stg}		-65 to +175	°C				

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS		
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	200	-	-			
Forward voltage		I _F = 5 A, T _J = 125 °C	-	0.87	0.99	V		
	V _F	I _F = 10 A, T _J = 125 °C	-	1.02	1.20			
		I _F = 10 A	-	1.12	1.25			
Povoroo lookago ourront		V _R = V _R rated	-	-	10			
Reverse leakage current I _R		$T_J = 150 \text{ °C}, V_R = V_R \text{ rated}$	-	-	250	μA		
Junction capacitance	CT	V _R = 200 V	-	8	-	pF		
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8.0	-	nH		



RoHS COMPLIANT HALOGEN

FREE

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DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS		
		$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t =$	50 A/µs, V _R = 30 V	-	-	35		
Boyoroo roooyory timo	+	I _F = 0.5 A, I _R = 1.0 A, I _{REC} = 0.25 A		-	-	25	ns	
Reverse recovery time	t _{rr}	T _J = 25 °C		-	24	-	115	
		T _J = 125 °C		-	35	-		
Dook rooovery ourrent		T _J = 25 °C	I _F = 5 A dI _F /dt = 200 A/μs V _R = 160 V	-	3.3	-	A	
Peak recovery current	I _{RRM}	T _J = 125 °C		-	5.0	-	~	
Reverse recovery charge	0	T _J = 25 °C		-	33	-	20	
	Q _{rr}	T _J = 125 °C		-	76	-	nC	

THERMAL - MECHANICAL SPECIFICATIONS								
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS		
Maximum junction and storage temperature range	T _J , T _{Stg}		-65	-	175	°C		
Thermal resistance, junction to case per leg	R _{thJC}		-	-	5			
Thermal resistance, junction to ambient per leg	R _{thJA}		-	-	50	°C/W		
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.5	-			
Weight			-	2.0	-	g		
weight			-	0.07	-	oz.		
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)		
Marking device		Case style TO-220AB		MUR1020CT				

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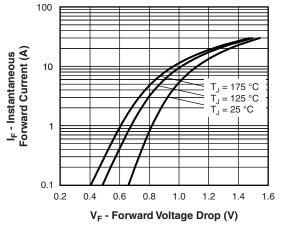
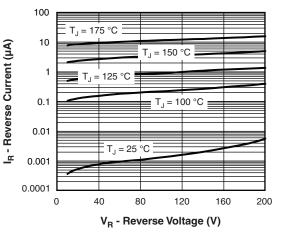
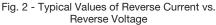


Fig. 1 - Typical Forward Voltage Drop Characteristics





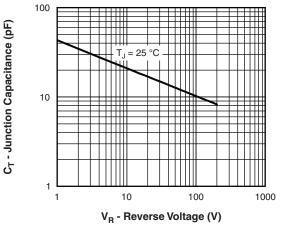


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

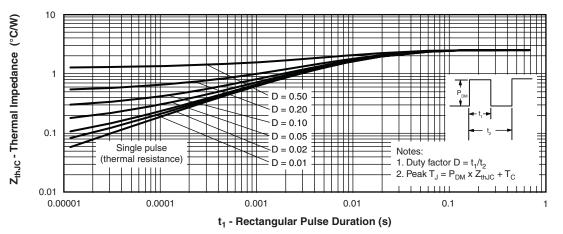
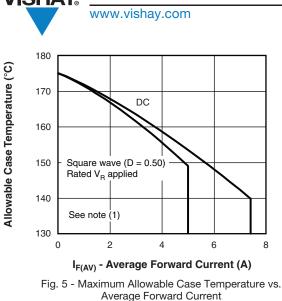


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

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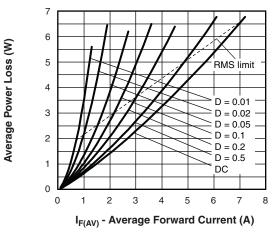
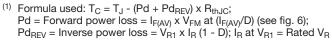


Fig. 6 - Forward Power Loss Characteristics

Note



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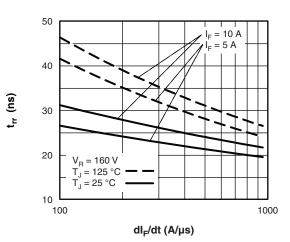


Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

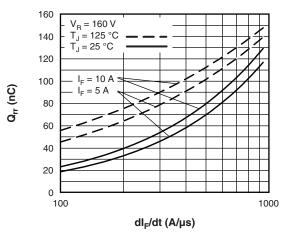


Fig. 8 - Typical Stored Charge vs. dl_F/dt

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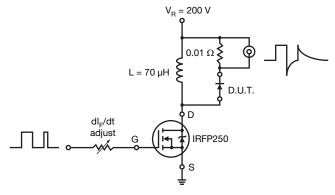
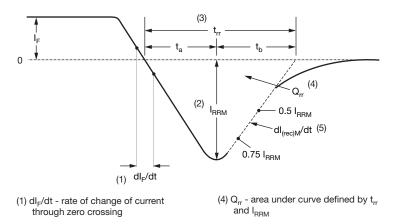


Fig. 9 - Reverse Recovery Parameter Test Circuit



(2) I_{RRM} - peak reverse recovery current

(3) t_{rr} - reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.

 $Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$ (5) $dI_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

Fig. 10 - Reverse Recovery Waveform and Definitions

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ORDERING INFORMATION TABLE

Device code	VS-	MUR	10	20	СТ	PbF		
		2	3	4	5	6		
	 Vishay Semiconductors product Ultrafast MUR series 							
	3 - Current rating (10 = 10 A)							
	4 - Voltage rating (20 = 200 V)							
	5 - CT = center tap (dual) TO-220/D ² PAK/TO-262							
	6	- Env	ironmer	ntal digit	:			
		PbF	= lead	(Pb)-fre	e and R	loHS-co	mpliant	

-N3 = halogen-free, RoHS-compliant and totally lead (Pb)-free

ORDERING INFORMATION (Example)							
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION				
VS-MUR1020CTPbF	50	1000	Antistatic plastic tube				
VS-MUR1020CT-N3	50	1000	Antistatic plastic tube				

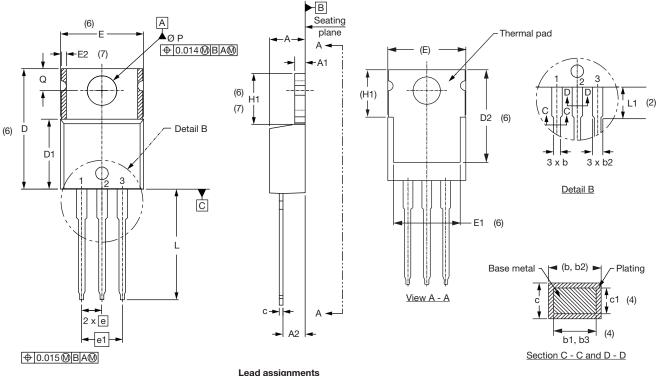
LINKS TO RELATED DOCUMENTS					
Dimensions		www.vishay.com/doc?95222			
Dout mouling information	TO-220ABPbF	www.vishay.com/doc?95225			
Part marking information	TO-220AB-N3	www.vishay.com/doc?95028			

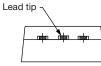


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TO-220AB

DIMENSIONS in millimeters and inches





Ľ	ea	a	a	ssi	g	пп	ne	20	IU
					-				

<u>Diodes</u>

Anode/open
 Cathode
 Anode

SYMBOL	MILLIM	LIMETERS INCHES		HES	NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.25	4.65	0.167	0.183	
A1	1.14	1.40	0.045	0.055	
A2	2.56	2.92	0.101	0.115	
b	0.69	1.01	0.027	0.040	
b1	0.38	0.97	0.015	0.038	4
b2	1.20	1.73	0.047	0.068	
b3	1.14	1.73	0.045	0.068	4
С	0.36	0.61	0.014	0.024	
c1	0.36	0.56	0.014	0.022	4
D	14.85	15.25	0.585	0.600	3
D1	8.38	9.02	0.330	0.355	
D2	11.68	12.88	0.460	0.507	6

Notes

- ⁽¹⁾ Dimensioning and tolerancing as per ASME Y14.5M-1994
- ⁽²⁾ Lead dimension and finish uncontrolled in L1
- ⁽³⁾ Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- ⁽⁴⁾ Dimension b1, b3 and c1 apply to base metal only
- ⁽⁵⁾ Controlling dimensions: inches
- $^{(6)}$ Thermal pad contour optional within dimensions E, H1, D2 and E1

MILLIMETERS INCHES SYMBOL NOTES MIN. MAX. MIN. MAX. 0.414 10.11 10.51 0.398 3,6 Е E1 6.86 8.89 0.270 0.350 6 E2 0.76 0.030 7 --2.41 2.67 0.095 0.105 е 0.208 e1 4.88 5.28 0.192 H1 6.09 6.48 0.240 0.255 6,7 13.52 14.02 0.532 0.552 Т 3.32 3.82 0.131 0.150 2 L1 ØΡ 3.54 3.73 0.139 0.147 0.102 Q 2.60 3.00 0.118 90° to 93° 90° to 93° θ

Conforms to JEDEC outline TO-220AB

- $^{(7)}$ Dimensions E2 x H1 define a zone where stamping and singulation irregularities are allowed
- ⁽⁸⁾ Outline conforms to JEDEC TO-220, except A2 (maximum) and D2 (minimum) where dimensions are derived from the actual package outline



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